

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAlAs (P/N Type)

2. Electrode N(Cathode) Side Gold Alloy
 P(Anode) Side Gold Alloy

3. Electro-Optical Characteristics

Parameter	Symbo	Min	Typ	Max	Unit	Condition
Forward Voltage	V_F		1.45	1.55	V	IF=100mA
Reverse Voltage	V_R	8			V	IR=10uA
Power	P_O	18	20		mW	IF=100mA
Wavelength	λ_P		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : Power is measured by Sorter E/T system with bare chip.

4. Mechanical Data

(a) Emission Area	-----	14.7mil x	14.7mil
(b) Bottom Area	-----	15.7mil x	15.7mil
(c) Bonding Pad	-----	135um	
(d) Chip Thickness	-----	11mil	
(e) Junction Height	-----	6.7mil	

